

General Description

The CMSC60P03 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON).

This device is ideal for load switch and battery protection applications.

Features

- P-Channel MOSFET
- Low ON-resistance
- Surface Mount Package
- RoHS Compliant

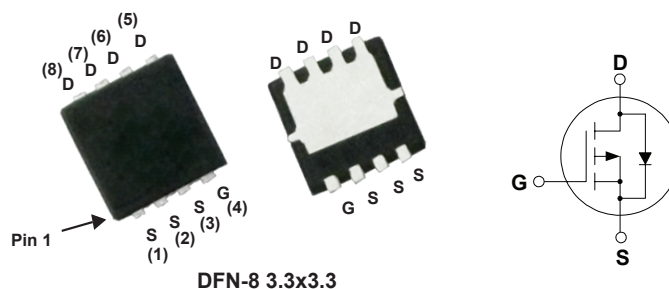
Product Summary

BVDSS	R _{DS(on)} max.	ID
-30V	8mΩ	-50A

Applications

- High side in DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook

DFN-8 3.3x3.3 Pin Configuration



DFN-8 3.3x3.3

Type	Package	Marking
CMSC60P03	DFN-8 3.3*3.3	60P03

Absolute Maximum Ratings (T_A=25 °C Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	-50	A
I _D @T _C =100°C	Continuous Drain Current	-40	A
I _{DM}	Pulsed Drain Current	-200	A
EAS	Single Pulse Avalanche Energy ¹	180	mJ
P _D @T _C =25°C	Total Power Dissipation	40	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance, Junction-to-Ambient	---	65	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30	---	---	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-28A$	---	---	8	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-25A$	---	---	17	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D = -250\mu A$	-1	---	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	5	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-15V$, $I_D=-15A$ $V_{GS}=-4.5V$	---	31	---	nC
Q_{gs}	Gate-Source Charge		---	11	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GEN}=-10V$, $I_D=-15A$ $R_G=3.3\Omega$	---	9	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	116	---	
T_f	Fall Time		---	23	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	2800	---	pF
C_{oss}	Output Capacitance		---	330	---	
C_{rss}	Reverse Transfer Capacitance		---	300	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_{SD}=-28A$	---	---	-1.2	V

Notes:

1. The test condition is $V_{DS}=-20V$, $V_{GS}=-10V$, $L=0.5mH$, $I_D=27A$.

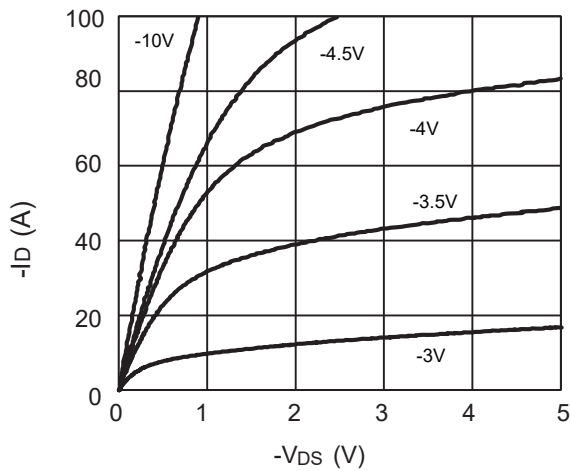
This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

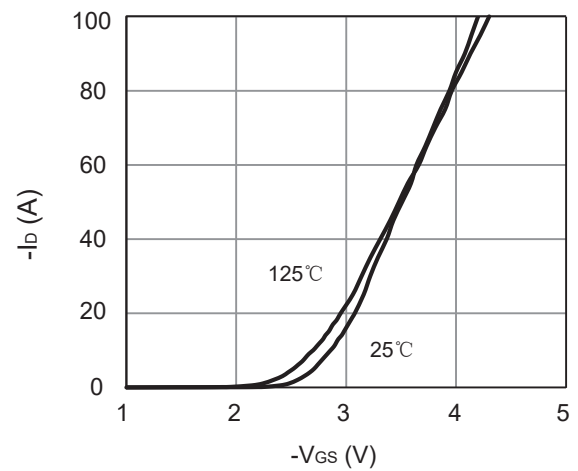
Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

P-Channel Enhancement Mode MOSFET

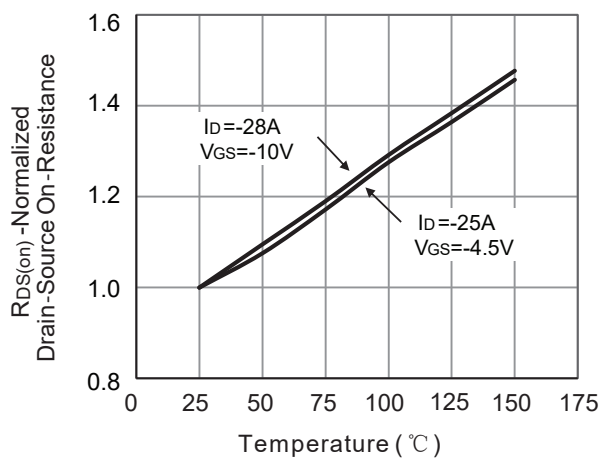
Typical Characteristics



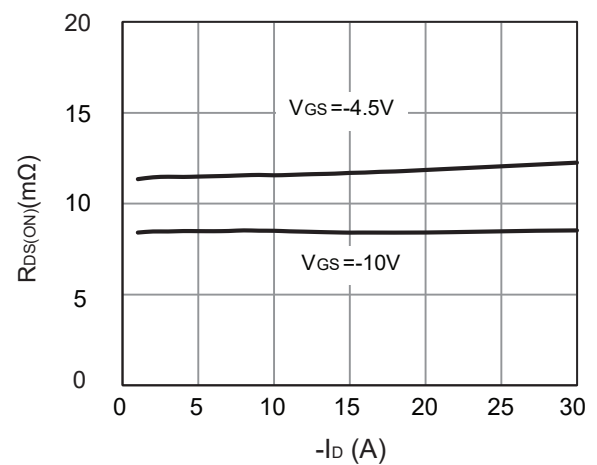
On-Region Characteristics



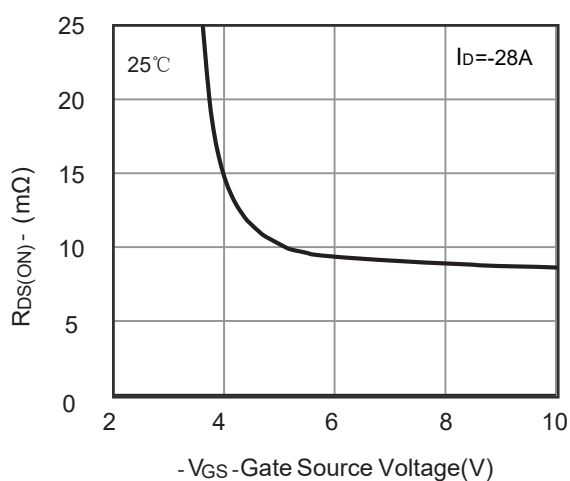
transfer characteristics



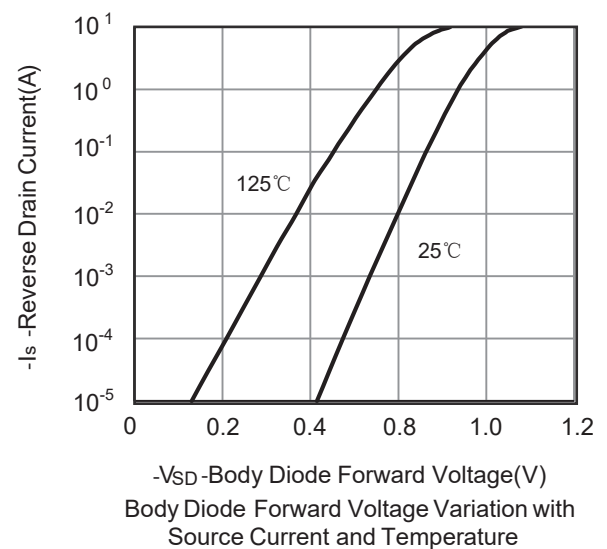
On-Resistance vs. Junction Temperature



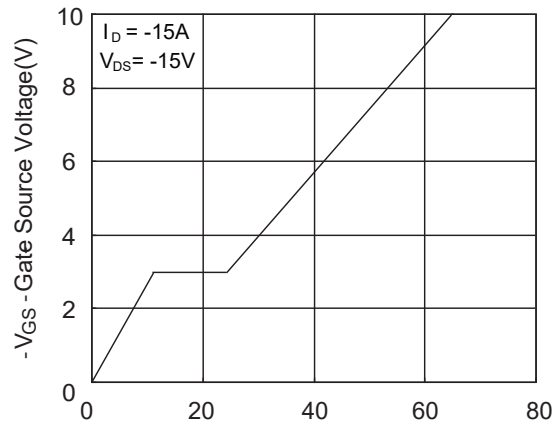
On-Resistance vs. Drain Current



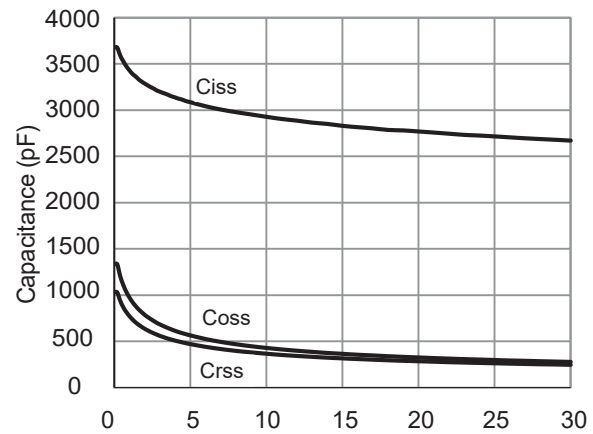
On-Resistance Variation with Gate-Source Voltage



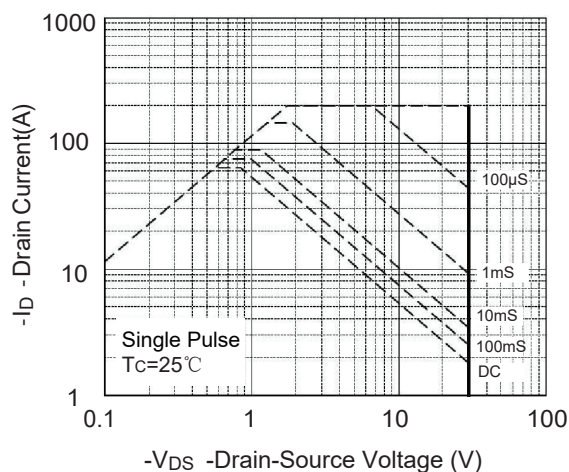
Typical Characteristics



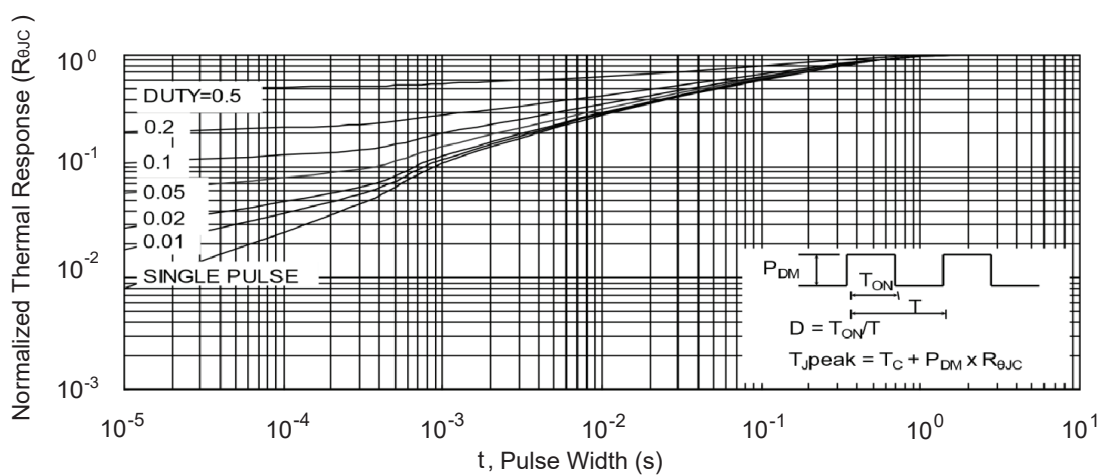
Gate Charge Characteristics



Capacitance Characteristics



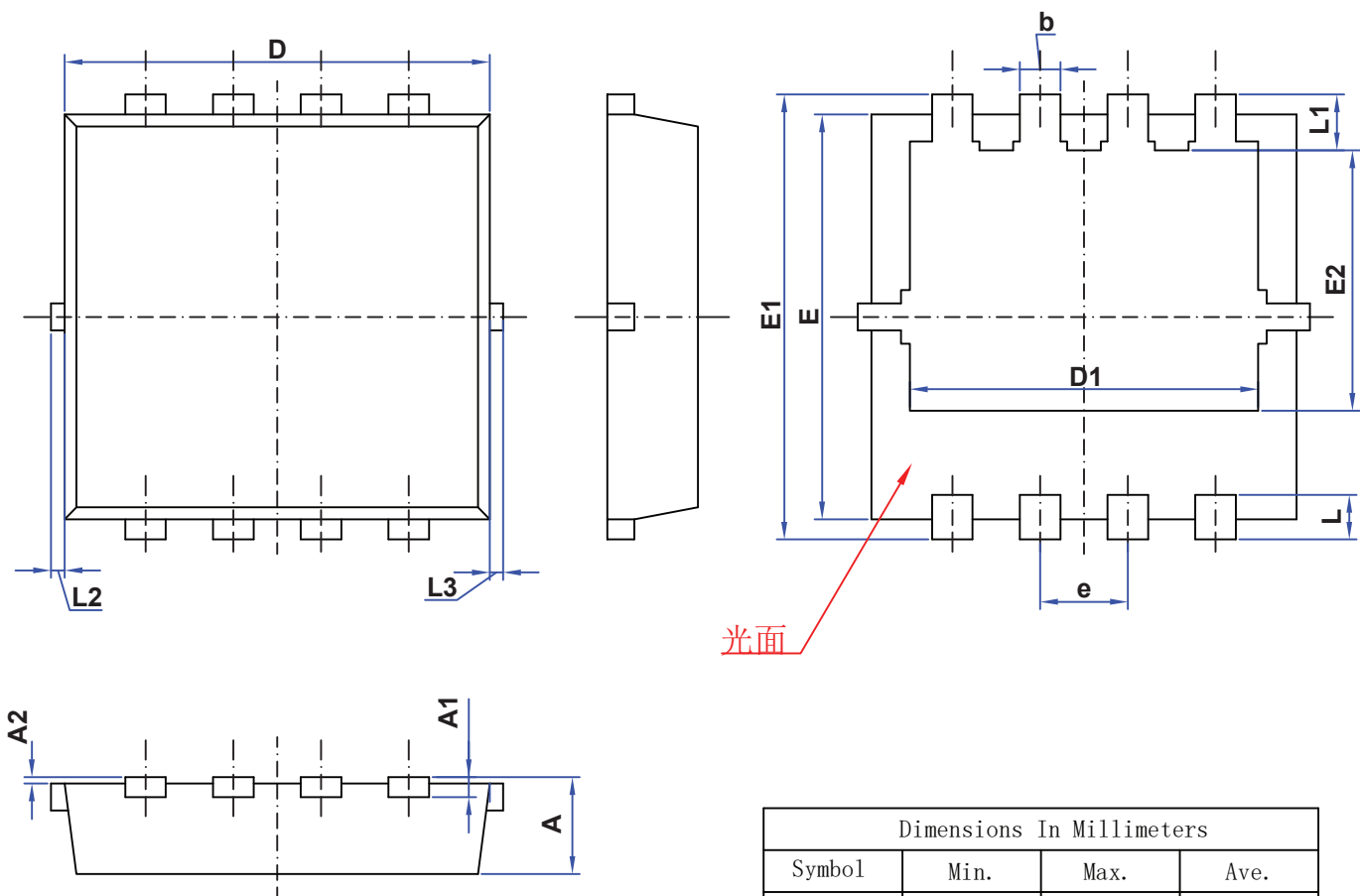
Safe Operating Area



Normalized Maximum Transient Thermal Impedance

Package Dimension

DFN-8 3.3x3.3 Unit :mm



- 注:
- 1. 未注公差±0.10,
 - 2. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
 - 3. 标注单位mm

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.700	0.900	0.800
A1	0.100	0.200	0.150
A2	-	0.050	-
D	3.000	3.200	3.100
D1	2.350	2.550	2.450
E	3.000	3.200	3.100
E1	3.200	3.600	3.400
E2	1.635	1.835	1.735
b	0.200	0.400	0.300
e	0.550	0.750	0.650
L	0.250	0.650	0.450
L1	0.345	0.745	0.545
L2	0~0.100		
L3	0~0.100		